

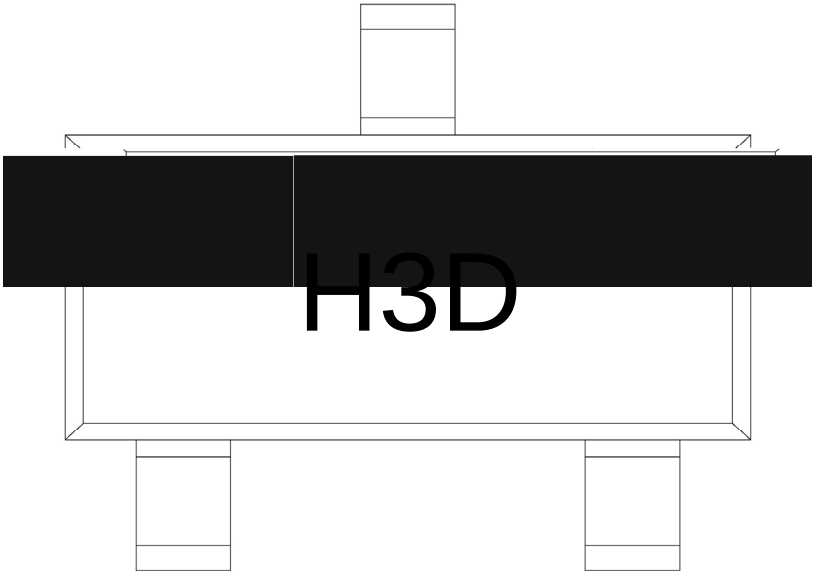
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	500	V
Collector to Emitter Voltage	V_{CEO}	400	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	300	mA
Collector Power Dissipation	P_C	350	mW
Collector Power Dissipation	$P_{C(TC=25)}$	1.5	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\mu A$ $I_E=0$	500			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	400			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=10\mu A$ $I_C=0$	6.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=400V$ $I_E=0$			0.1	μA
Collector Cut-Off Current	I_{CES}	$V_{CE}=400V$ $V_{BE}=0$			1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_C=0$			0.1	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=10V$ $I_C=10mA$	50		200	
	$h_{FE(2)}$	$V_{CE}=10V$ $I_C=100mA$	40			
	$h_{FE(3)}$	$V_{CE}=10V$ $I_C=50mA$	45			
	$h_{FE(4)}$	$V_{CE}=10V$ $I_C=1.0mA$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=1.0mA$ $I_B=0.1mA$			0.4	V
	$V_{CE(sat)(2)}$	$I_C=10mA$ $I_B=1.0mA$			0.5	V
	$V_{CE(sat)(3)}$	$I_C=50mA$ $I_B=5.0mA$			0.75	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=10mA$ $I_B=1.0mA$			0.75	V
Output Capacitance	C_{ob}	$V_{CB}=20V$ $f=1.0MHz$ $I_E=0$			7.0	pF

/ Marking Instructions



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Note:
K X Company Code
3D X Product Type Code

